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MAC218A6FP, MAC218A8FP MAC218A10FP

Preferred Devices


Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies.

- Blocking Voltage to 800 Volts
- Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Isolated TO-220 Type Package for Ease of Mounting
- Gate Triggering Guaranteed in Four Modes
-  Indicates UL Registered – File #E69369
- Device Marking: Logo, Device Type, e.g., MAC218A6FP, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)


Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1.) (T _J = -40 to +125°C, Sine Wave 50 to 60 Hz, Gate Open)	V _{DRM} , V _{RRM}	400 600 800	Volts
On-State RMS Current (T _C = +80°C) (Note 2.) Full Cycle Sine Wave 50 to 60 Hz	I _{T(RMS)}	8.0	Amps
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T _C = +80°C) Preceded and followed by rated current	I _{TSM}	100	Amps
Circuit Fusing Considerations (t = 8.3 ms)	I ² t	40	A ² s
Peak Gate Power (T _C = +80°C, Pulse Width = 10 μs)	P _{GM}	16	Watts
Average Gate Power (T _C = +80°C, t = 8.3 ms)	P _{G(AV)}	0.35	Watt
Peak Gate Current (T _C = +80°C, Pulse Width = 10 μs)	I _{GM}	4.0	Amps
RMS Isolation Voltage (T _A = 25°C, Relative Humidity ≤ 20%) 	V _(ISO)	1500	Volts
Operating Junction Temperature	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

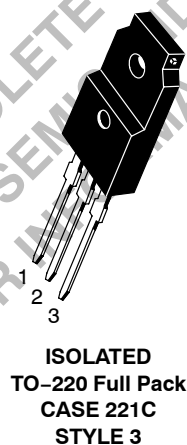
1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
2. The case temperature reference point for all T_C measurements is a point on the center lead of the package as close as possible to the plastic body.



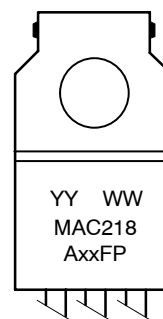
ON Semiconductor™

<http://onsemi.com>

**ISOLATED TRIAC ()
8 AMPERES RMS
400 thru 800 VOLTS**



MARKING DIAGRAM



**ISOLATED
TO-220 Full Pack
CASE 221C
STYLE 3**

MAC218AxxFP = Specific Device Code
xx = 6, 8 or 10
YY = Year
WW = Work Week

PIN ASSIGNMENT

Pin	Assignment
1	Main Terminal 1
2	Main Terminal 2
3	Gate

ORDERING INFORMATION

Device	Package	Shipping
MAC218A6FP	ISOLATED TO220FP	500/Box
MAC218A8FP	ISOLATED TO220FP	500/Box
MAC218A10FP	ISOLATED TO220FP	500/Box

Preferred devices are recommended choices for future use and best overall value.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2 (typ)	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	$^{\circ}\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{DRM}, V_{RRM}; \text{ Gate Open}$)	I_{DRM}, I_{RRM}	-	-	10	μA
		-	-	2.0	mA

ON CHARACTERISTICS

Peak On-State Voltage (Note 1) ($I_{TM} = \pm 11.3 \text{ A Peak}$)	V_{TM}	-	1.7	2.0	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ Vdc}, R_L = 100 \Omega$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	I_{GT}	-	-	50 50 50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100 \text{ Ohms}$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	V_{GT}	-	0.9 0.9 1.1 1.4	2.0 2.0 2.0 2.5	Volts
Gate Non-Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 V, $R_L = 100 \Omega, T_J = +125^{\circ}\text{C}$) All Four Quadrants	V_{GD}	0.2	-	-	Volts
Holding Current ($V_D = 12 \text{ Vdc}, \text{ Gate Open, Initiating Current} = \pm 200 \text{ mA}$)	I_H	-	-	50	mA

DYNAMIC CHARACTERISTICS

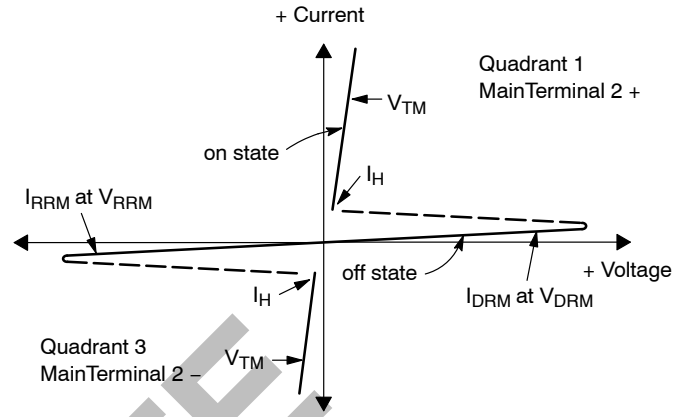
Critical Rate of Rise of Commutating Off-State Voltage ($V_D = \text{Rated } V_{DRM}, I_{TM} = 11.3 \text{ A}, \text{ Commutating } di/dt = 4.1 \text{ A/ms}, \text{ Gate Unenergized}, T_C = 80^{\circ}\text{C}$)	$dv/dt_{(c)}$	-	5.0	-	$\text{V}/\mu\text{s}$
Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}, \text{ Exponential Voltage Rise, Gate Open}, T_J = 125^{\circ}\text{C}$)	dv/dt	-	100	-	$\text{V}/\mu\text{s}$

1. Pulse Test: Pulse Width $\leq 2.0 \text{ ms}$, Duty Cycle $\leq 2\%$.

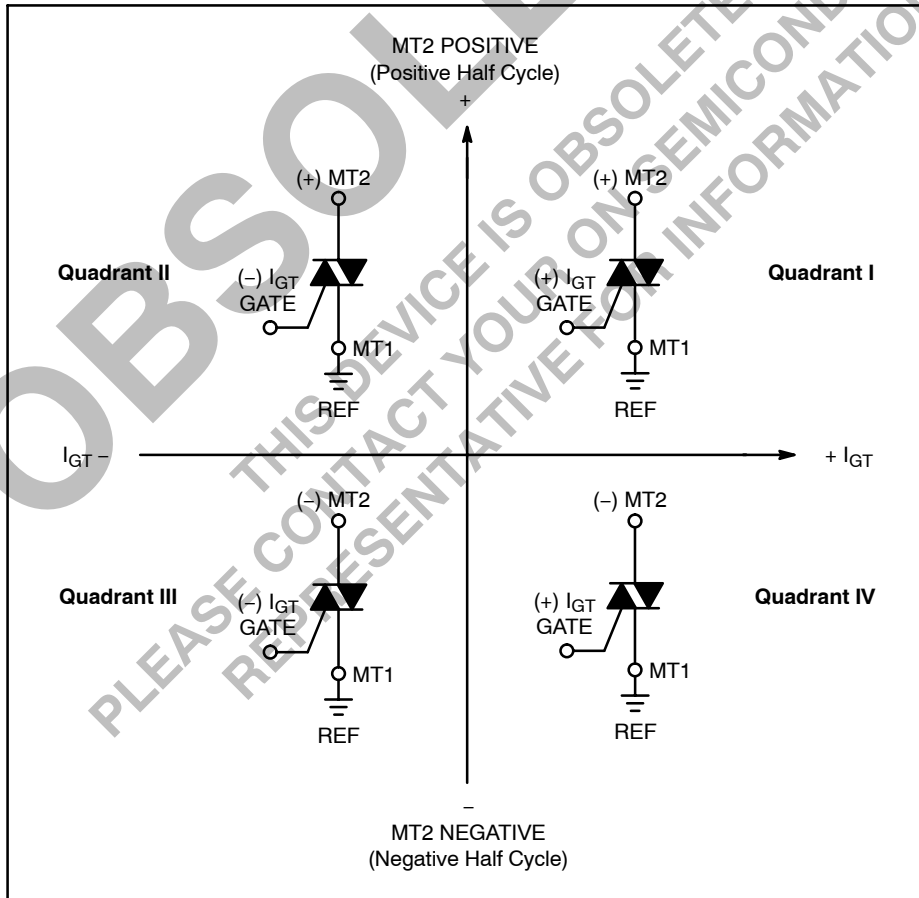
MAC218A6FP, MAC218A8FP MAC218A10FP

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.
With in-phase signals (using standard AC lines) quadrants I and III are used.

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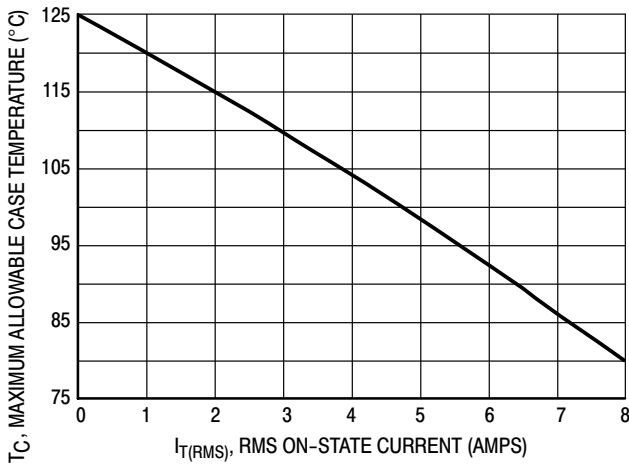


Figure 1. Current Derating

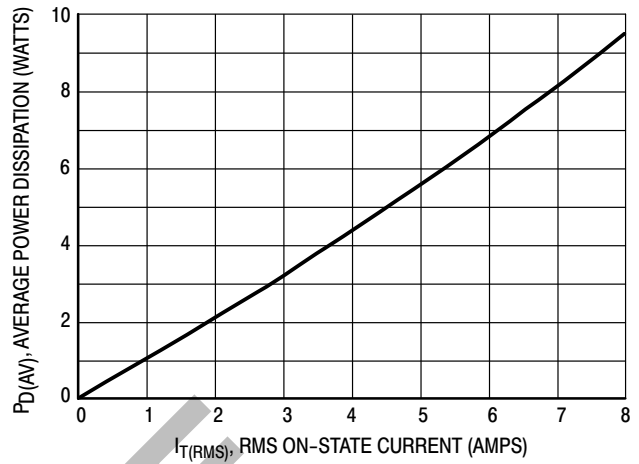


Figure 2. Power Dissipation

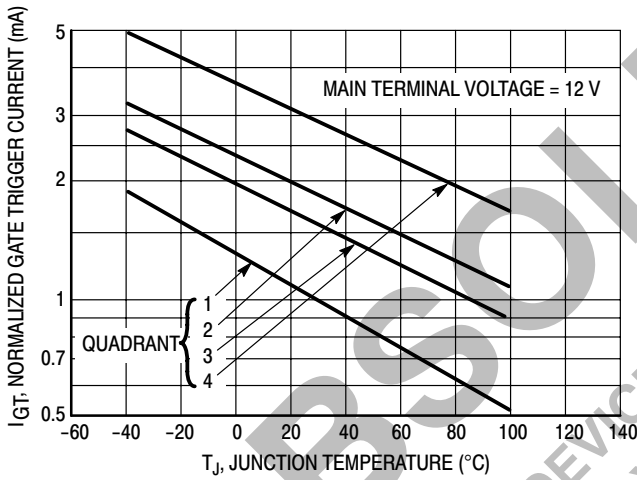


Figure 3. Normalized Gate Trigger Current

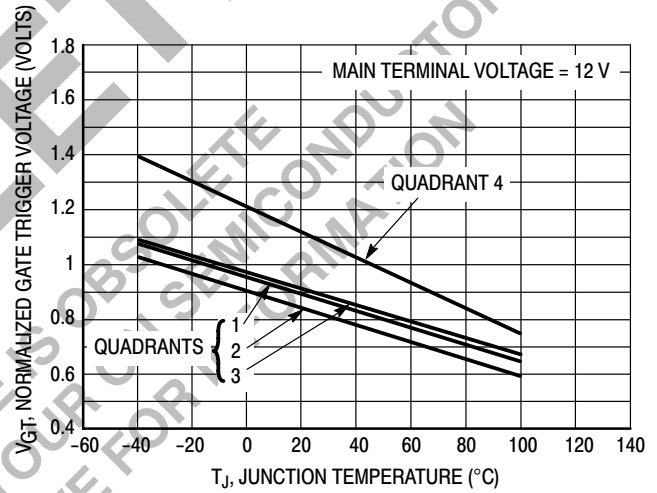


Figure 4. Normalized Gate Trigger Voltage

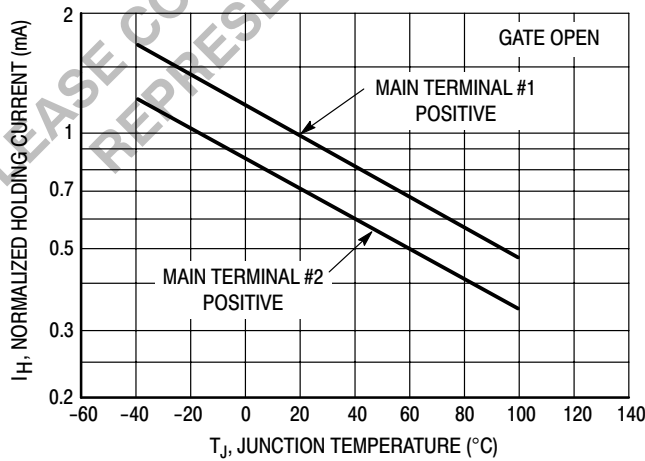
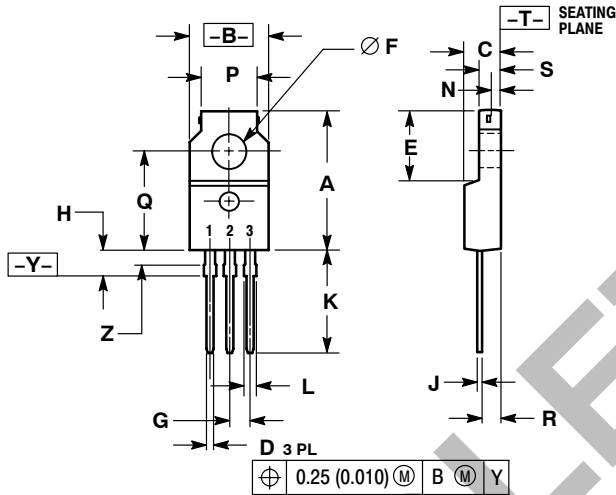


Figure 5. Normalized Holding Current

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PACKAGE DIMENSIONS

TO-220 FULLPACK THYRISTOR CASE 221C-02 ISSUE D



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.680	0.700	17.28	17.78
B	0.388	0.408	9.86	10.36
C	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
E	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54 BSC	
H	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049	---	1.25	---
P	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

STYLE 3:

1. MT 1
2. MT 2
3. GATE

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